L Number	Hits	Search Text	DB	Time stamp
- NUMBEL	0	(""densified dielectric"").PN.	USPAT; US-PGPUB;	2002/07/18 16:18
_		(""densified"").PN.	EPO; JPO USPAT;	2002/07/18
			US-PGPUB; EPO; JPO	17:15
-	0	("densified").PN.	USPAT	2002/07/18 17:15
-	8939	densification	USPAT	2002/07/18 17:15
-	71	densification near dielectric	USPAT	2002/07/18
-	616	densification same dielectric	USPAT	2002/07/18 17:15
-	25	(densification near dielectric) and	USPAT	2002/07/18
-	697	"low k dielectric"	USPAT; US-PGPUB;	2002/07/18 17:23
-	105	"low k dielectric" same "etch stop"	EPO; JPO USPAT; US-PGPUB;	2002/07/18 17:38
-	1	6054379.pn.	EPO; JPO USPAT	2002/07/18 17:48
-	271	treat\$3 near dielectric	USPAT; US-PGPUB;	2002/07/18 17:49
-	87	(treat\$3 near dielectric) and plasma	EPO; JPO USPAT; US-PGPUB;	2002/07/18 17:53
-	11	((treat\$3 near dielectric) and plasma) and "etch stop"	EPO; JPO USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:56
-	2	5314845.pn.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:58
~	2	5915203.pn.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:00
-	2	("6303047" "6365528").pn.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:06
-	44591	silicon with carbide	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:06
-	42528	silicon with carbon	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:07
-	73891	(silicon with carbide) or (silicon with carbon)	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:07
-	19286	((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:09
-	189	N2 nitrogen) (((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:10
-	167	N2 nitrogen)) and "low k" ((((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen)) and "low k") and	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:10
_	1620	"dual damascene" and etch\$3	USPAT; US-PGPUB;	2002/07/19 09:40
-	110	("dual damascene" and etch\$3) and "etch mask"	EPO; JPO USPAT; US-PGPUB; EPO; JPO	2002/07/19 09:40

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-	103		USPAT;	2002/07/19
		mask") and (vias via trenches trench)	US-PGPUB;	09:42
	Ì		EPO; JPO	1
-	101		USPAT;	2002/07/19
1	ì	mask") and (vias via trenches trench))	US-PGPUB;	09:42
	J	and pattern\$3	EPO; JPO	
-	39	(((("dual damascene" and etch\$3) and	USPAT:	2002/07/19
		"etch mask") and (vias via trenches	US-PGPUB:	09:49
	1	trench)) and pattern\$3) and "low k"	EPO; JPO	
-	1511	convert\$3 near6 dielectric	USPAT;	2002/07/19
	1		US-PGPUB;	09:54
			EPO; JPO	1
-	452	(convert\$3 near6 dielectric) and etch\$	USPAT;	2002/07/19
		(are	US-PGPUB;	09:55
1			EPO; JPO	03.33
-	5.9	((convert\$3 near6 dielectric) and etch\$)	USPAT;	2002/07/19
Į.	1	and ("etch mask" "etch stop")	US-PGPUB;	09:55
1		and (even mask even stop)	EPO; JPO	09.55
l _	226	photoresist adj mask adj5 dielectric	USPAT;	2003/05/14
1	220	photoresist adj mask adjs dielectic	EPO; JPO	21:25
_		(photoresist add mask add5 dielectric)	USPAT;	2003/05/14
-		and "densified dielectric"	EPO; JPO	21:24
	221	(photoresist adj mask adj5 dielectric)	USPAT;	2003/05/14
-	221	and etch\$3	EPO; JPO	21:25
_	3240		USPAT;	2003/05/14
	3240	eccuss adjs sidewall	EPO; JPO	21:25
_	10	(photoresist add mask add5 dielectric)	USPAT:	2003/05/14
_	1	and (etch\$3 adj3 sidewall)	EPO; JPO	21:30
_	2493		USPAT:	2003/10/09
1	2433	104 K 104 K	EPO; JPO	13:48
_	1450	("low-k" "low k") with dielectric	USPAT:	2003/10/09
1	1130	(10W K 10W K / WICH dielectile	EPO; JPO	13:49
I - I	712	(("low-k" "low k") with dielectric) and	USPAT;	2003/10/09
1	/12	damascene	EPO: JPO	13:49
_	532	((("low-k" "low k") with dielectric) and	USPAT:	2003/10/09
1	332	damascene) and plasma	EPO; JPO	13:49
	528	(((("low-k" "low k") with dielectric) and	USPAT:	2003/10/09
i i	320	damascene) and plasma) and etch\$3	EPO; JPO	13:49
l _	10632	"etch stop" "etch mask"	USPAT;	2003/10/09
-	10632	etch stop etch mask	EPO: JPO	13:49
_	309	("etch stop" "etch mask") and	USPAT;	2003/10/09
1 -	309	((((("low-k" "low k") with dielectric)	EPO; JPO	14:03
	į .	and damascene) and plasma) and etch\$3)	EPO, JPO	14:03
1		6.028.015.pn.	USPAT:	2003/10/09
1	1	6,026,015.pn.	EPO; JPO	14:04
		6 030 015 1 1		
-	1	6,028,015.pn. and photoresist	USPAT;	2003/10/09
	, ,	6 030 015	EPO; JPO	14:08
[-	1	6,028,015.pn. and mask	USPAT;	2003/10/09
			EPO; JPO	14:09
I -	1	6,028,015.pn. and pattern\$3	USPAT;	2003/10/09
	l	L	EPO; JPO	14:09